

Supporting information for

Comparative study on Schottky contact behaviors between Ga- and N-polar GaN with SiN_x interlayer

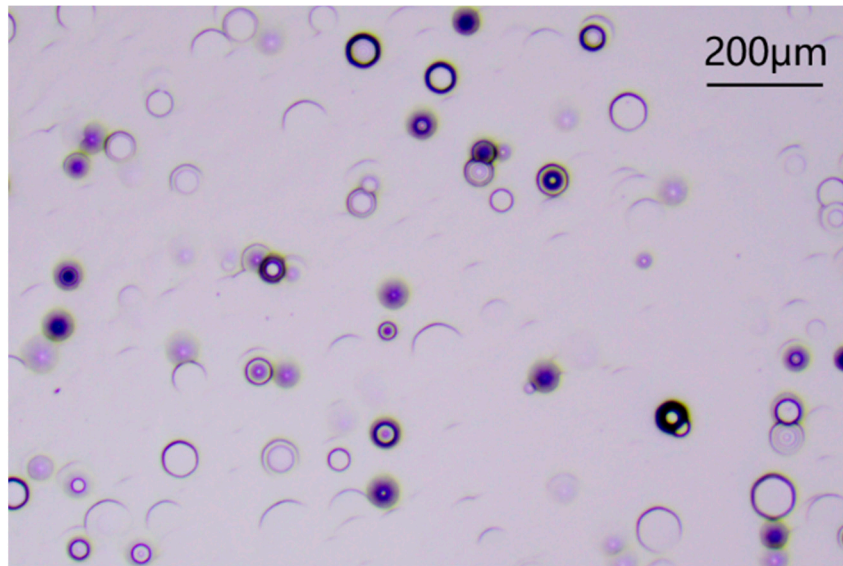


Figure S1. Optical microscope image showing the distribution and density of the hillocks on N-polar GaN

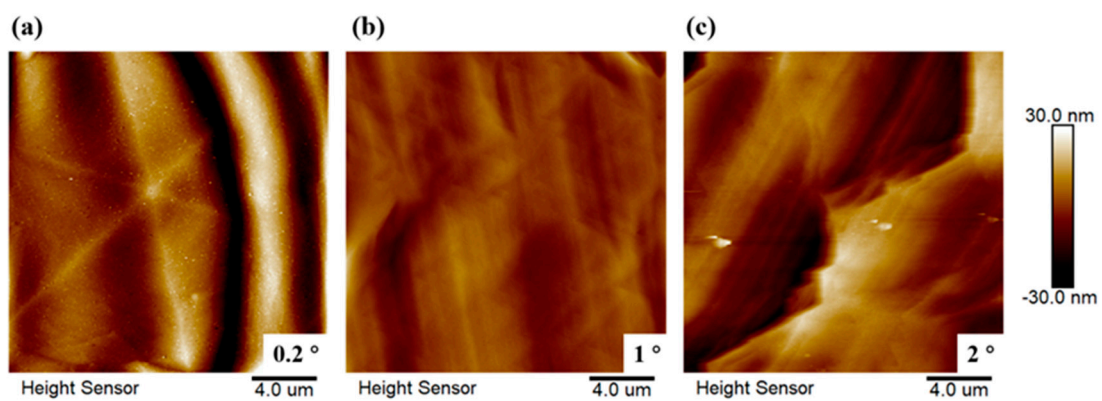


Figure S2. Surface morphologies of N-polar GaN grown on 0.2°, 1° and 2° misoriented substrate.

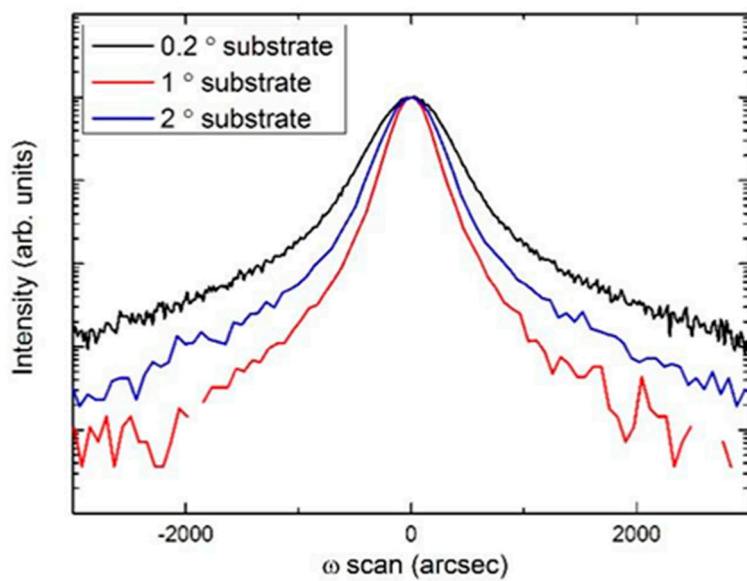


Figure S3. XRD (002) rocking curves of N-GaN grown on sapphire with various misorientation angles.

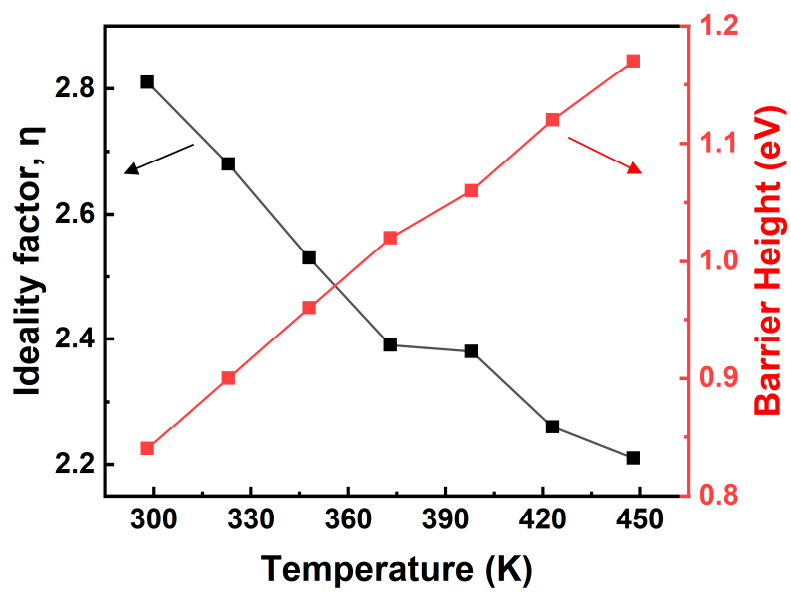


Figure S4. Temperature-dependent ideality factor and barrier height of Ga-polar MIS Schottky barrier height.